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TITLE: Method of fabricating shallow trench isolation

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Next, a dielectric layer 17 is formed to fill into the shallow trenches 12. The dielectric layer 17 is silicon oxide formed by using plasma-enhanced chemical vapor deposition (PECVD). Then, the dielectric layer 17 is etched back by using the method of chemical mechanical polishing (CMP) as shown in

FIG. 2F. The polysilicon layer 21 serves as an etching stop layer for this etching back process. Finally, the polysilicon layer 21 and the pad oxide layer 13 are removed, and a shallow trench isolation 12 is then obtained as shown in FIG. 2G.